

This Page Is Inserted by IFW Operations
and is not a part of the Official Record

BEST AVAILABLE IMAGES

Defective images within this document are accurate representations of the original documents submitted by the applicant.

Defects in the images may include (but are not limited to):

- BLACK BORDERS
- TEXT CUT OFF AT TOP, BOTTOM OR SIDES
- FADED TEXT
- ILLEGIBLE TEXT
- SKEWED/SLANTED IMAGES
- COLORED PHOTOS
- BLACK OR VERY BLACK AND WHITE DARK PHOTOS
- GRAY SCALE DOCUMENTS

IMAGES ARE BEST AVAILABLE COPY.

As rescanning documents *will not* correct images,
please do not report the images to the
Image Problem Mailbox.

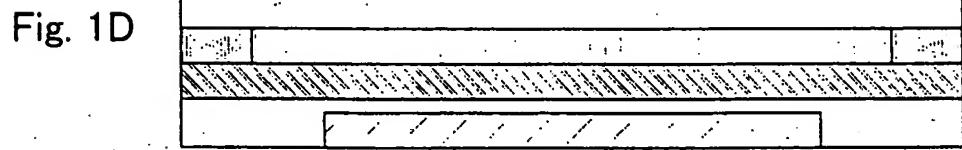
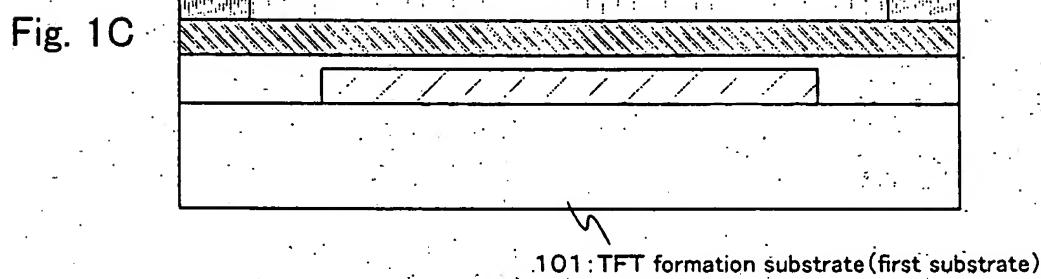
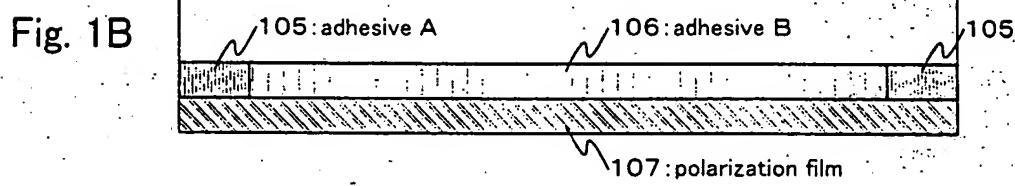
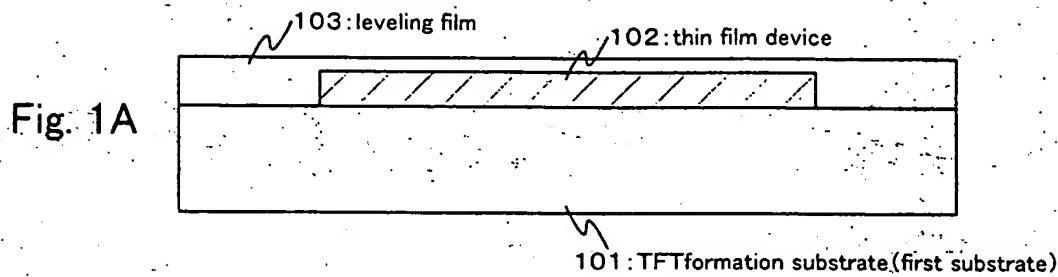


Fig. 2A

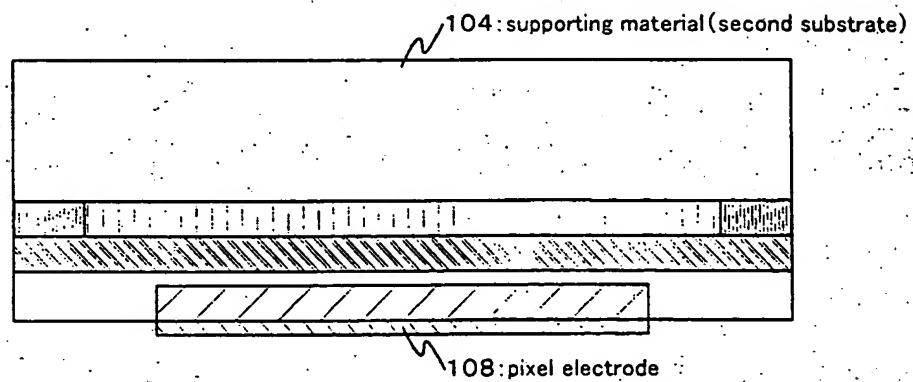


Fig. 2B

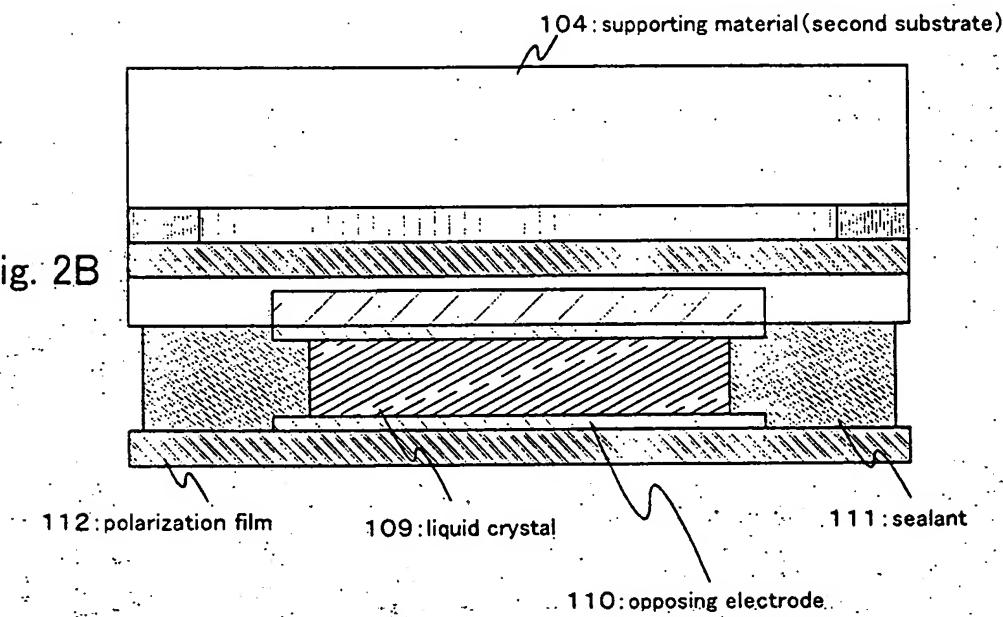


Fig. 3A

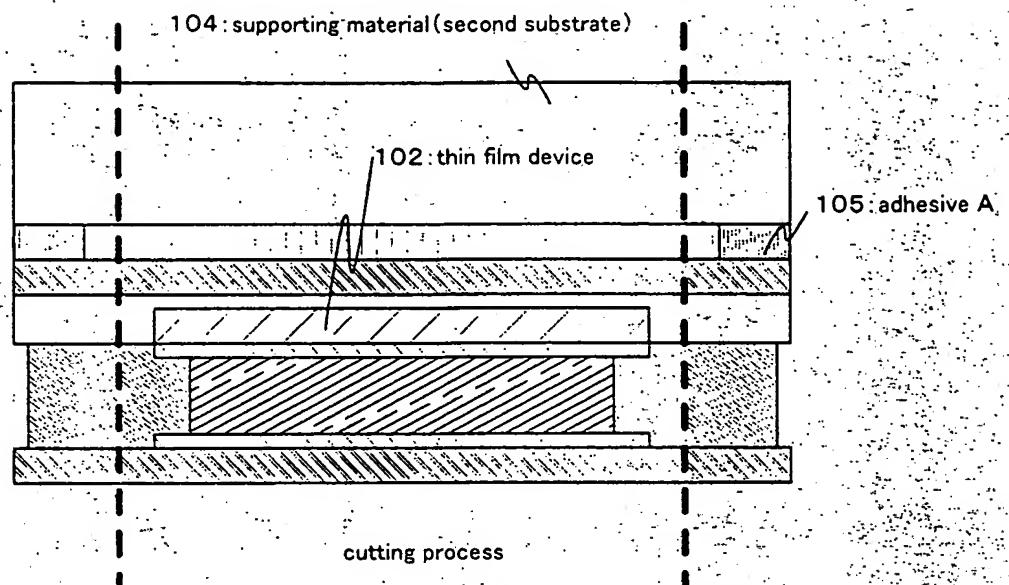


Fig. 3B

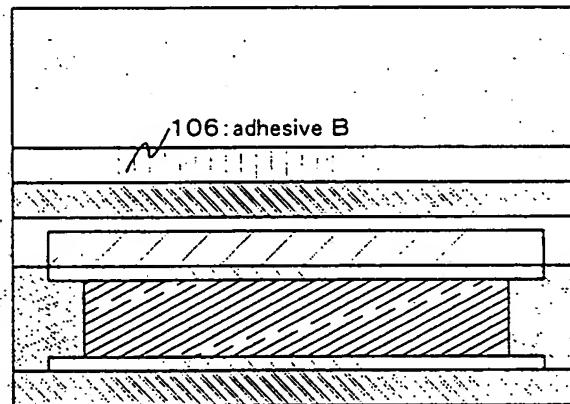
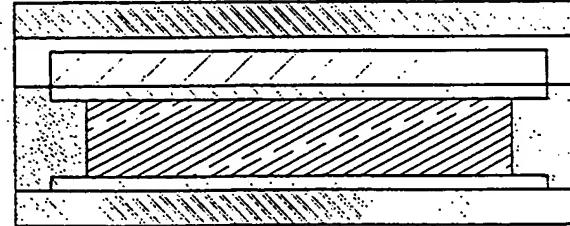


Fig. 3C



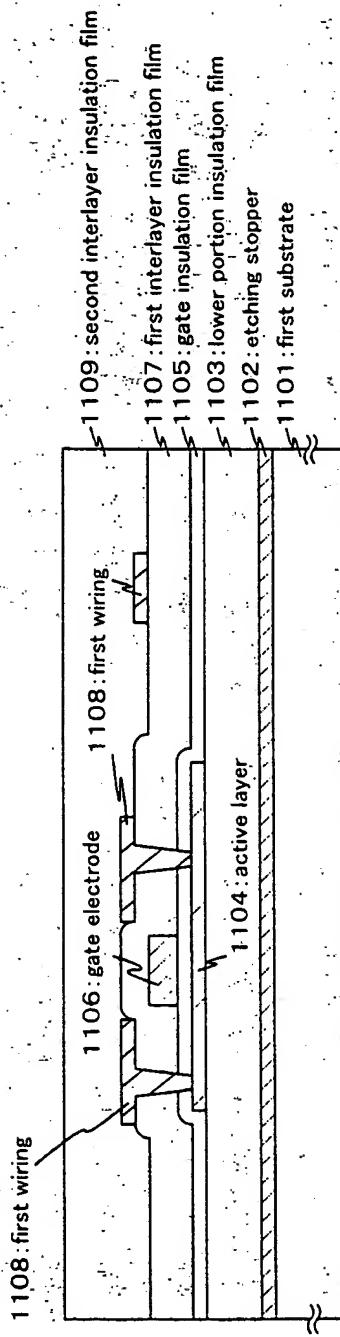


Fig. 4A

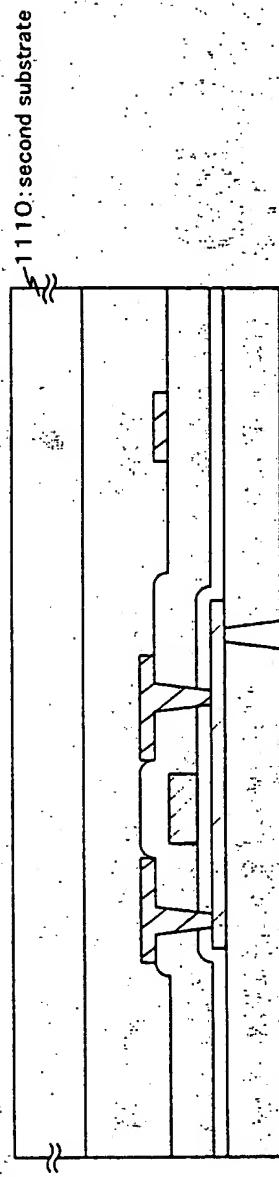


Fig. 4B

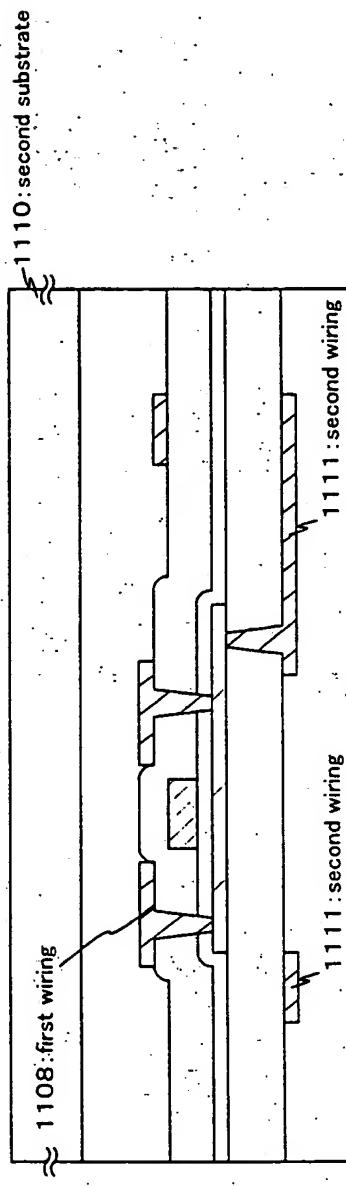


Fig. 5A

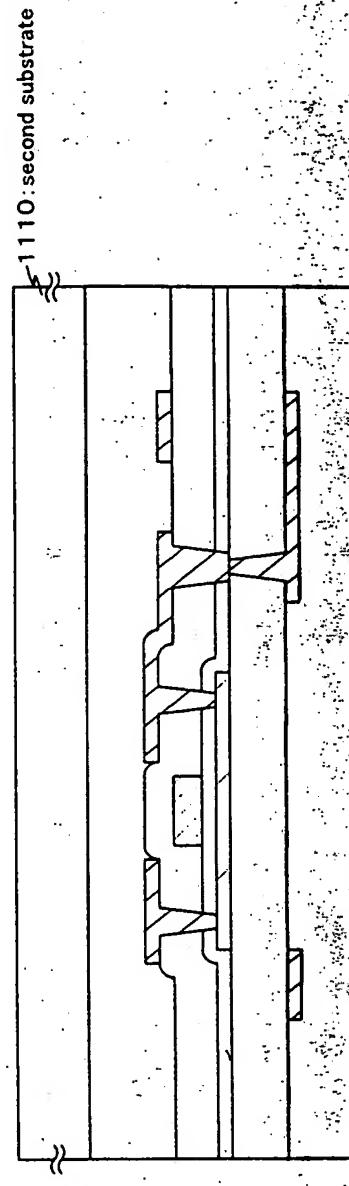


Fig. 5B

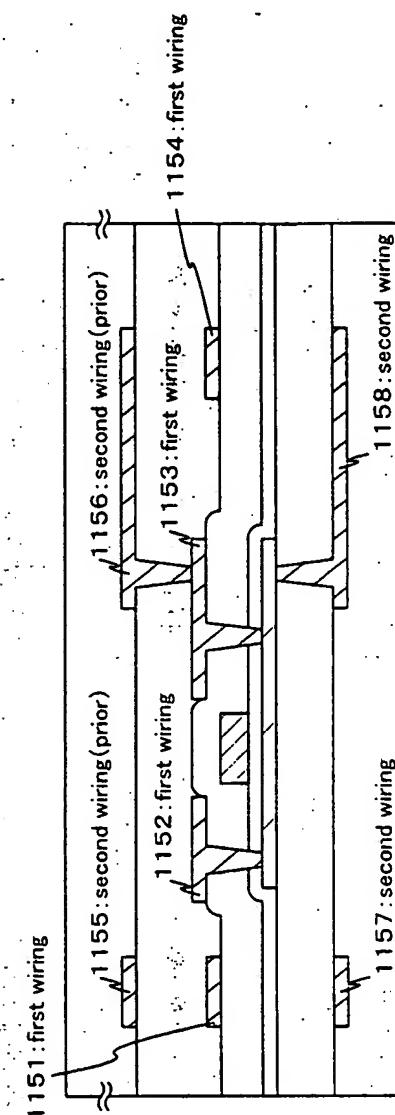


Fig. 6

Fig. 7A ≈

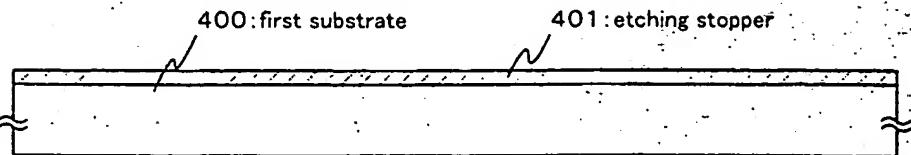


Fig. 7B ≈

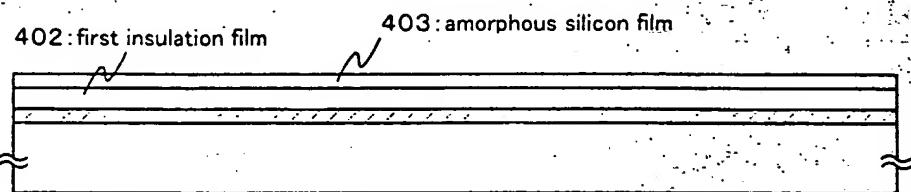


Fig. 7C ≈

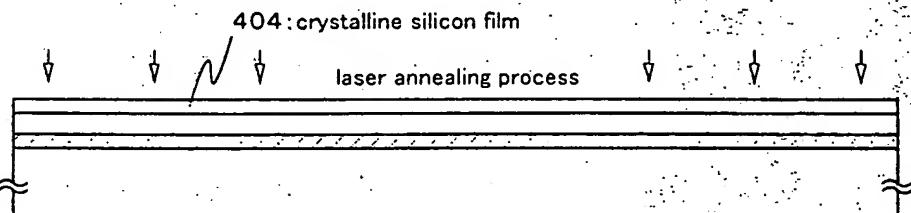


Fig. 7D ≈

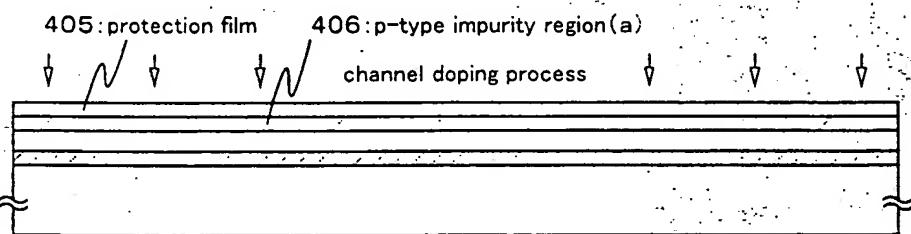


Fig. 7E ≈

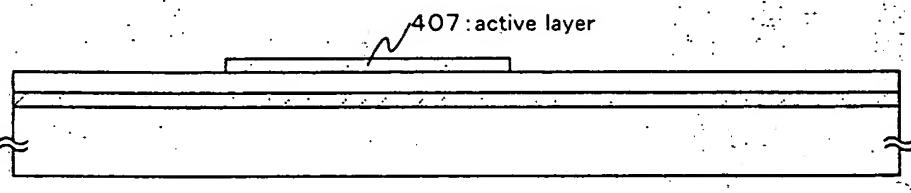


Fig. 7F ≈

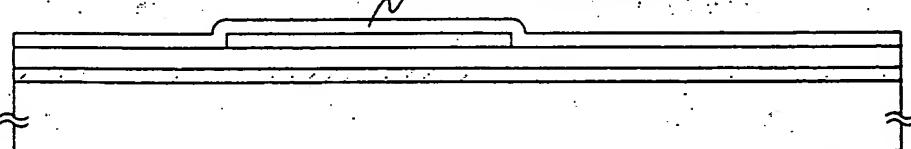


Fig. 8A

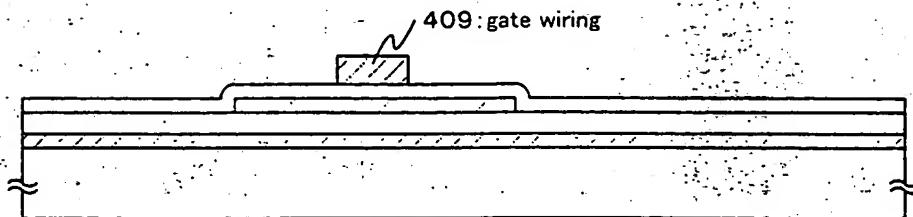


Fig. 8B

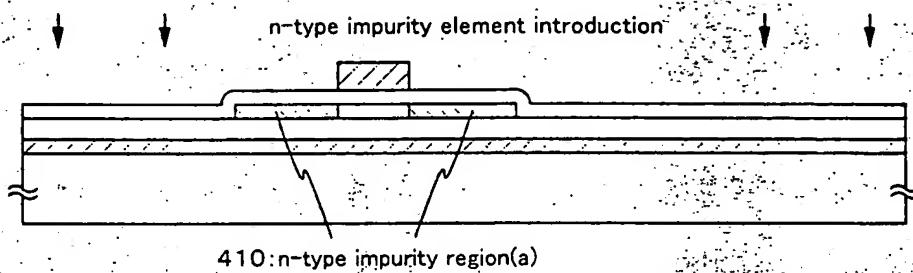


Fig. 8C

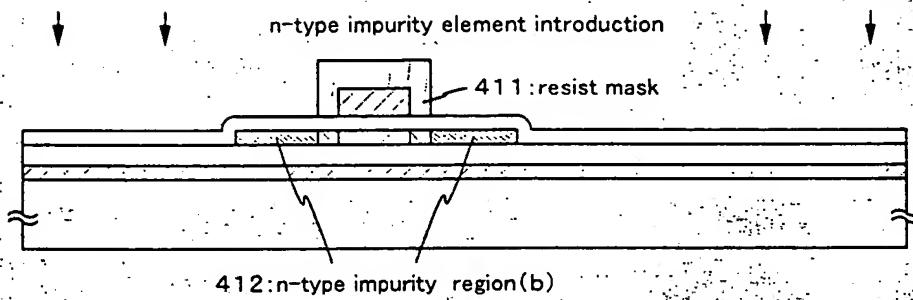


Fig. 8D

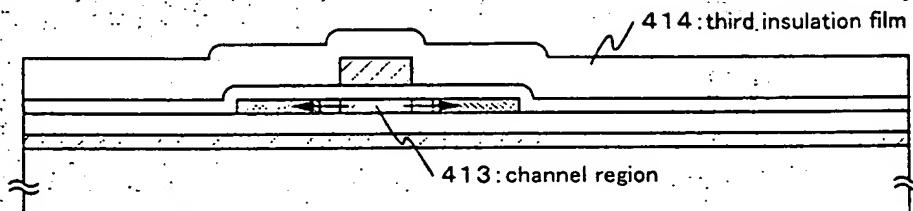


Fig. 9A

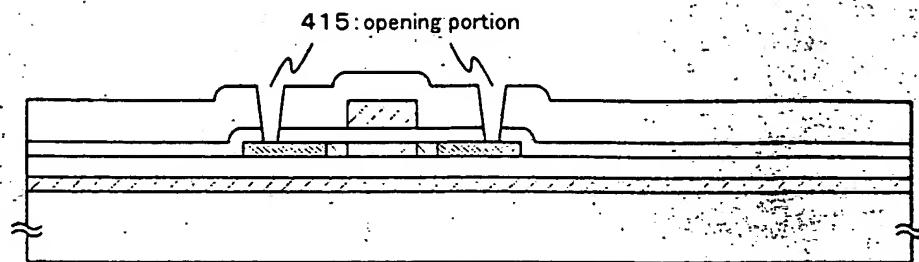


Fig. 9B

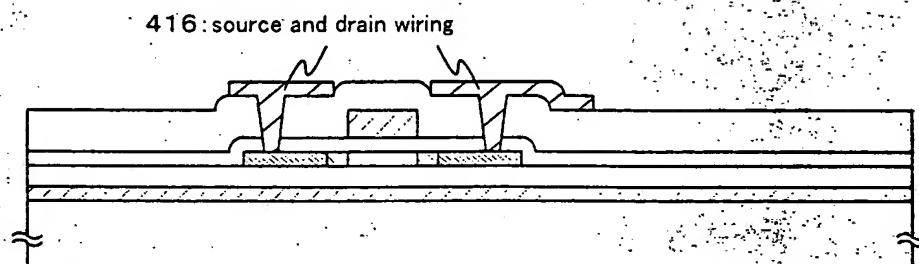


Fig. 9C

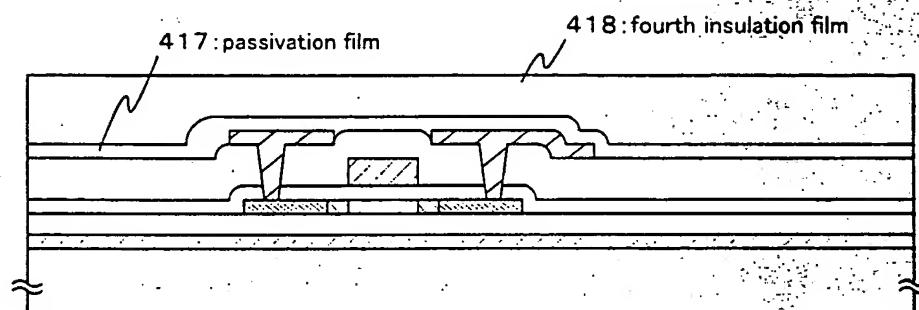


Fig. 9D

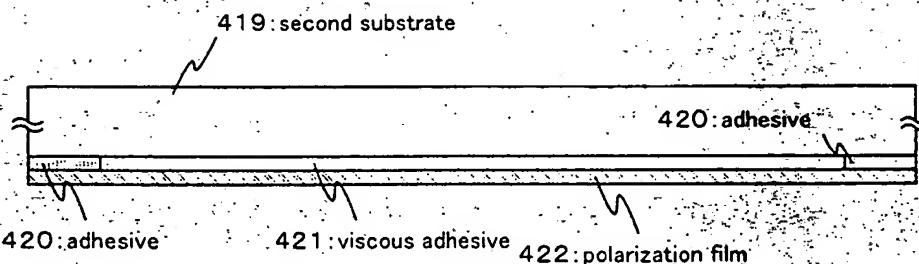


Fig. 10A

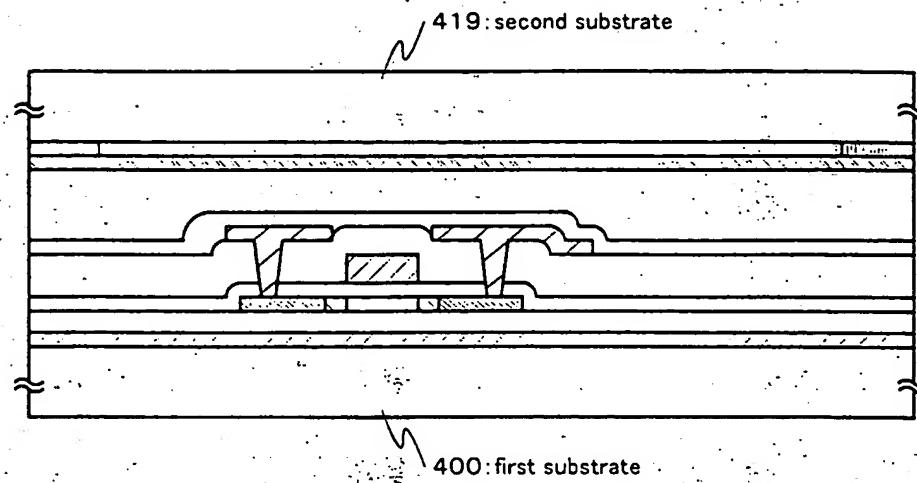


Fig. 10B

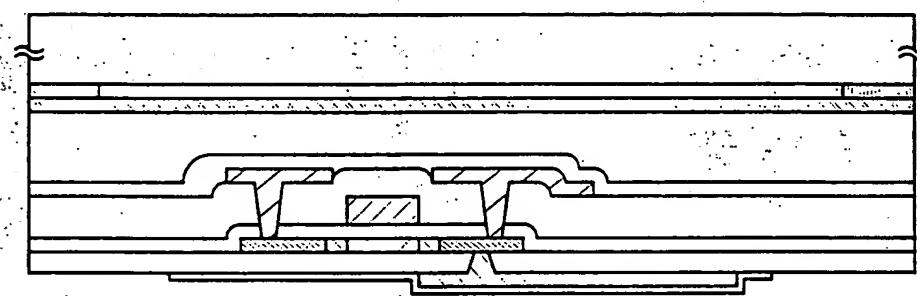
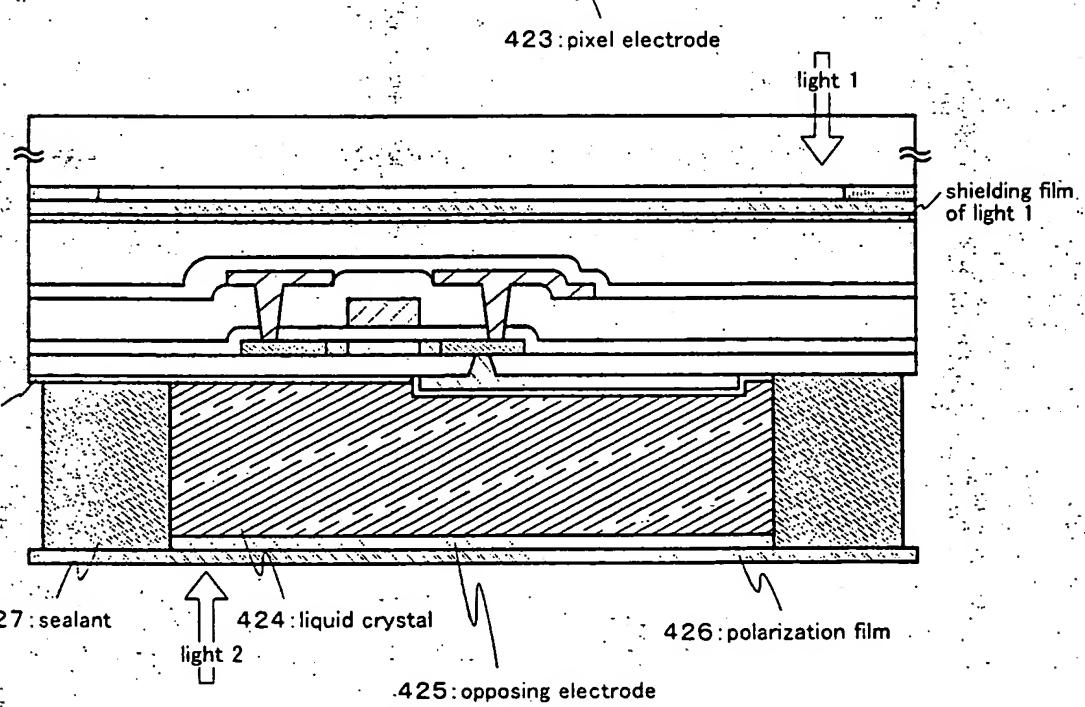
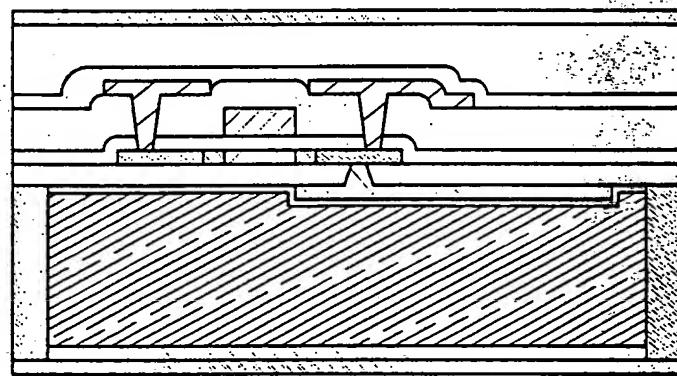
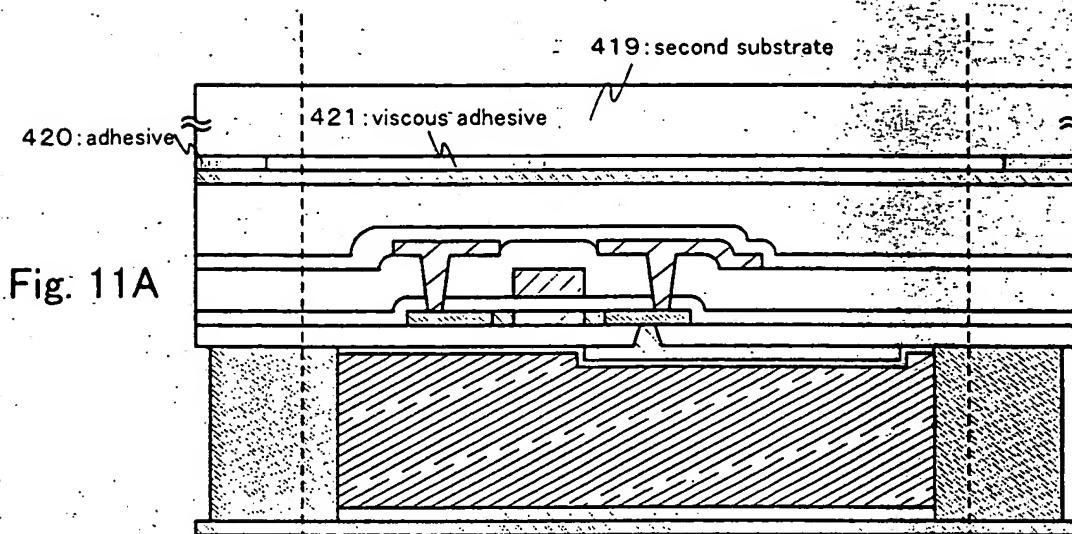


Fig. 10C





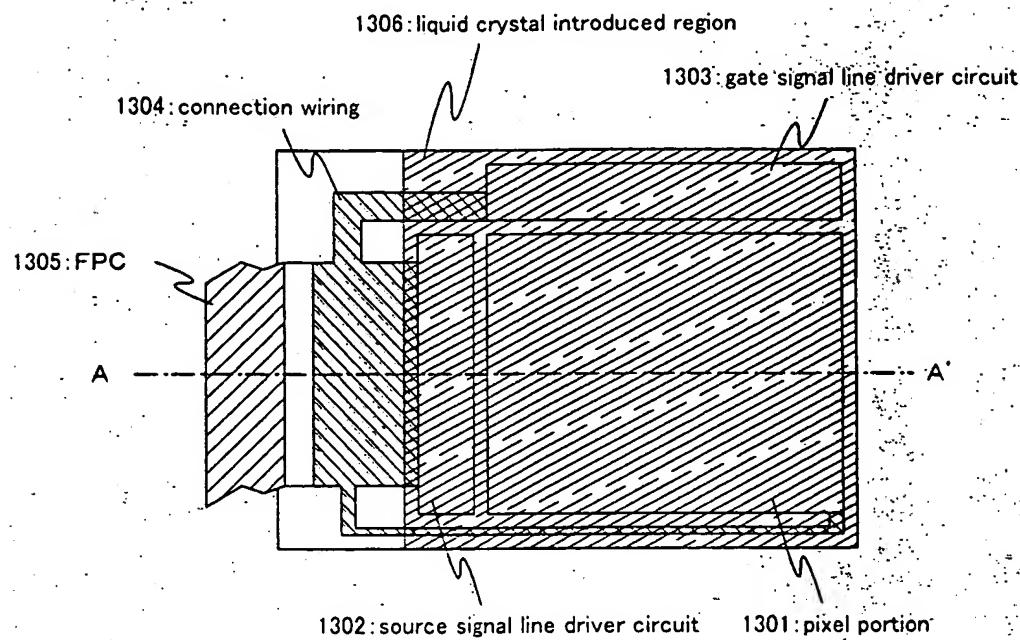


Fig. 12

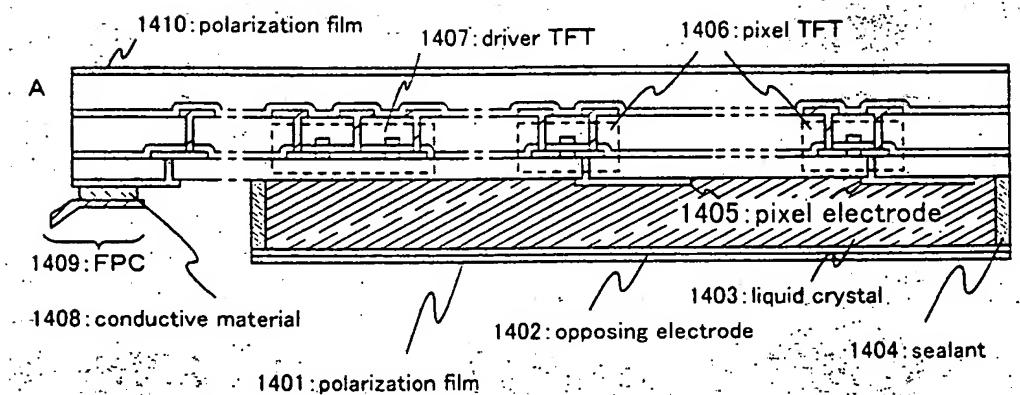


Fig. 13

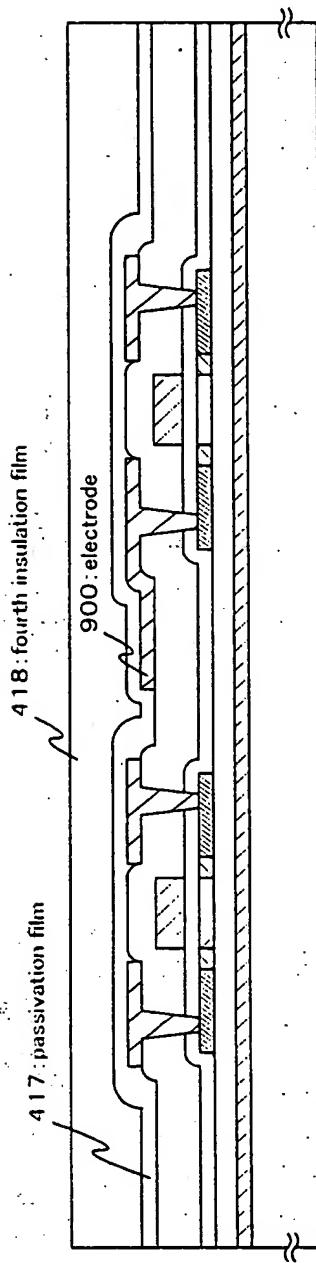


Fig. 14A

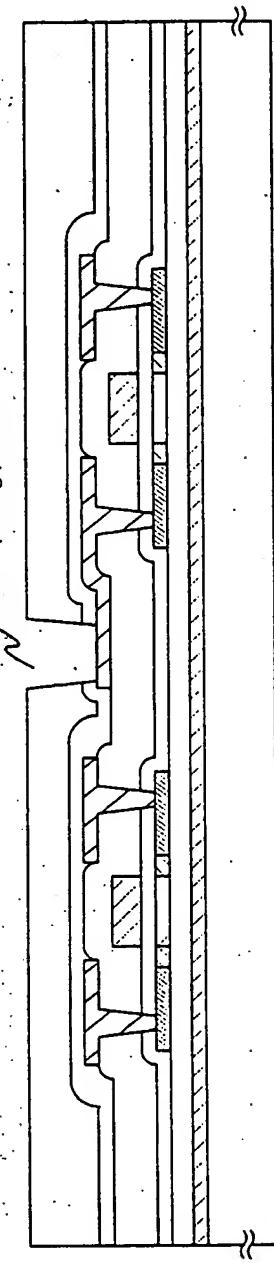


Fig. 14B

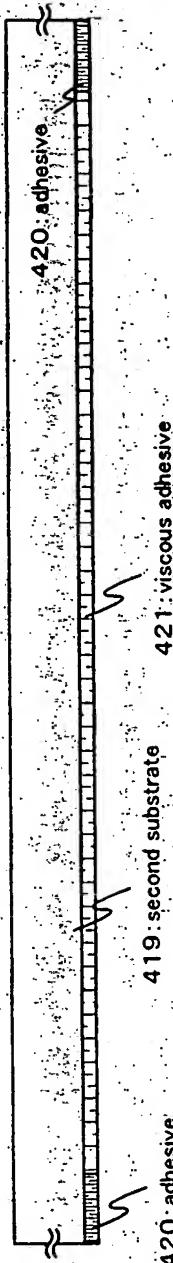


Fig. 14C

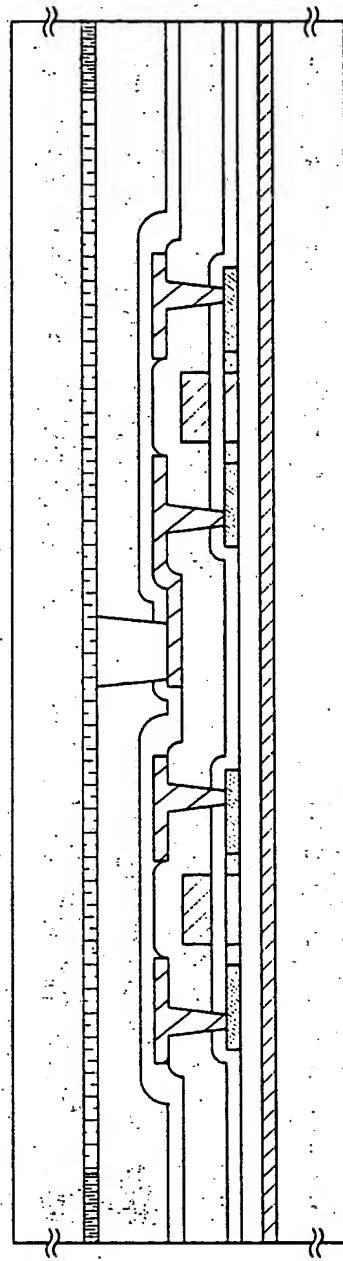


Fig. 15A

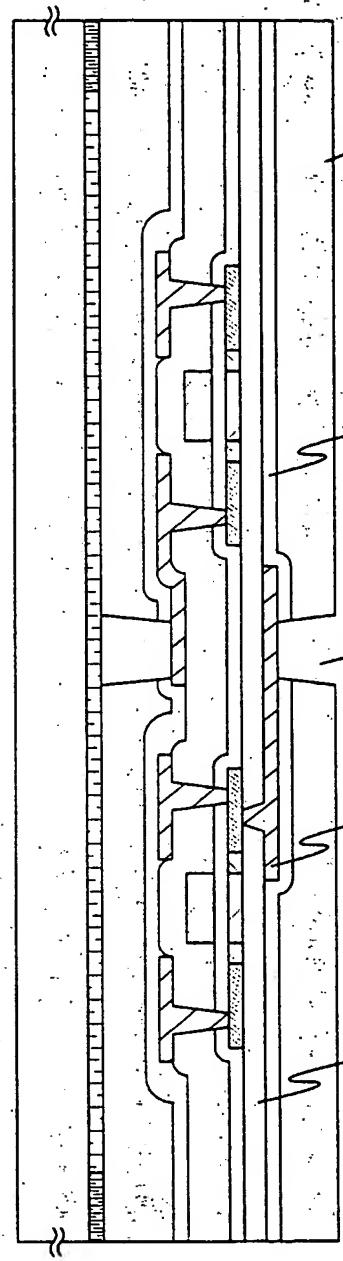


Fig. 15B

402: first insulation film 902: electrode 903: passivation film 905: opening portion
904: fifth insulation film

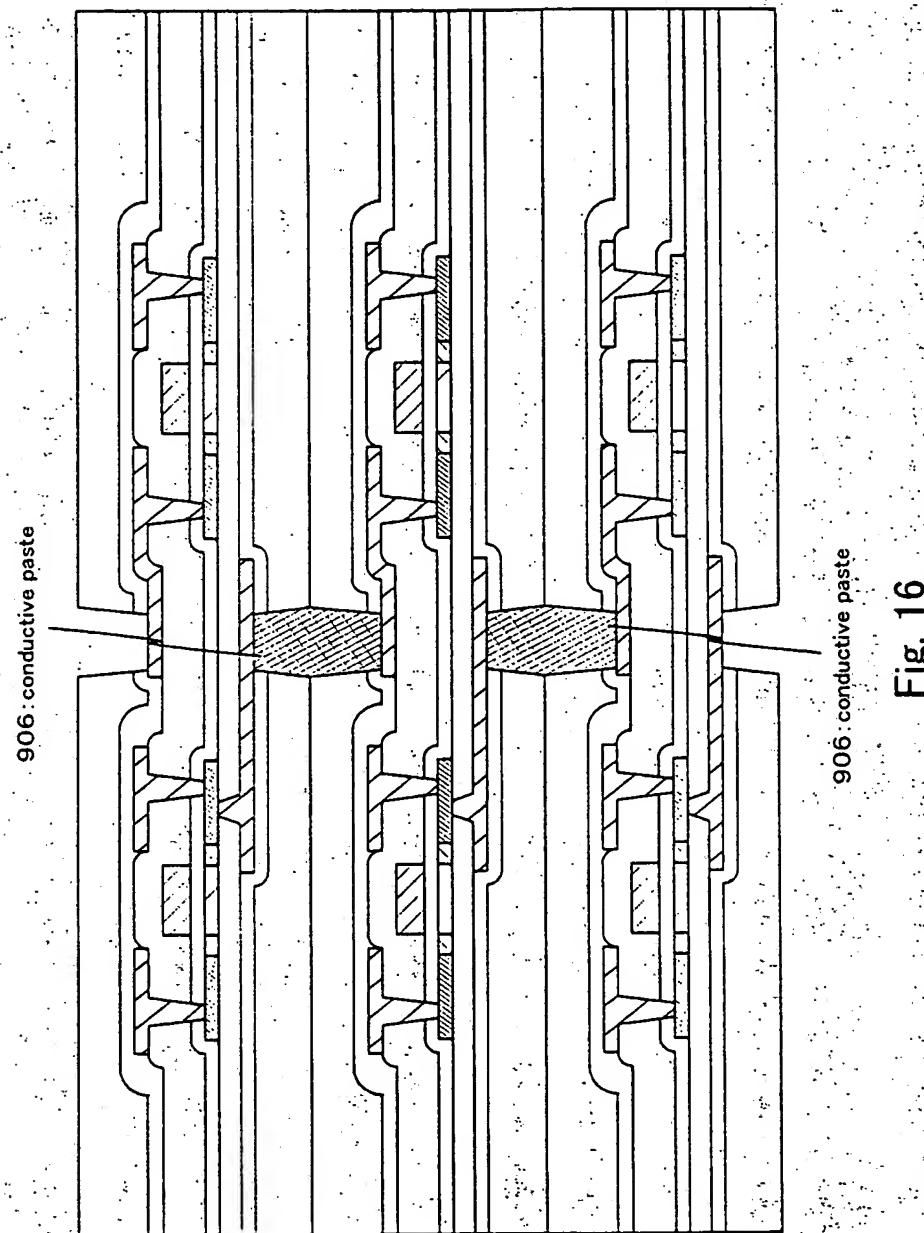
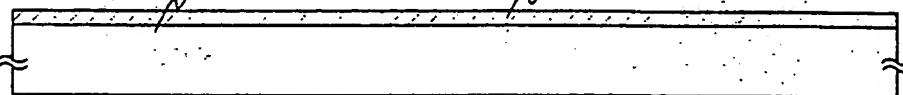


Fig. 16

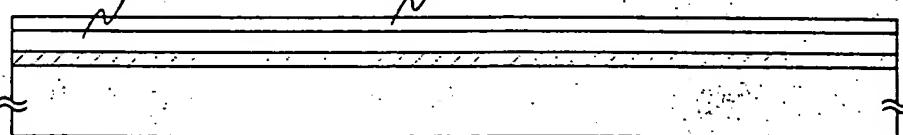
2401: first substrate 2402: etching stopper

Fig. 17A ≈



2403: lower portion insulation film 2404: amorphous silicon film

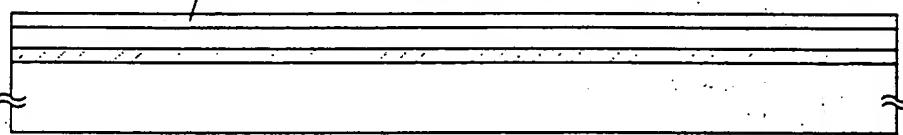
Fig. 17B ≈



2405: crystalline silicon film

laser annealing process

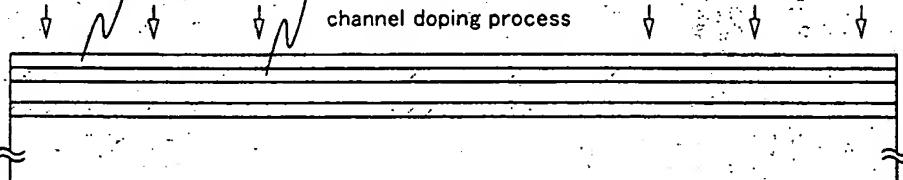
Fig. 17C ≈



2406: protection film 2407: p-type impurity region (a)

channel doping process

Fig. 17D ≈



2408: active layer

Fig. 17E ≈

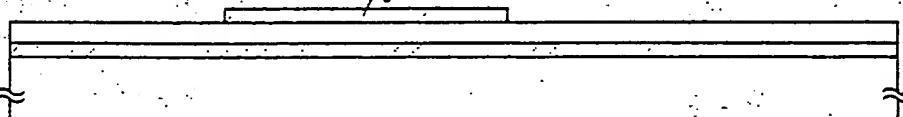


Fig. 18A

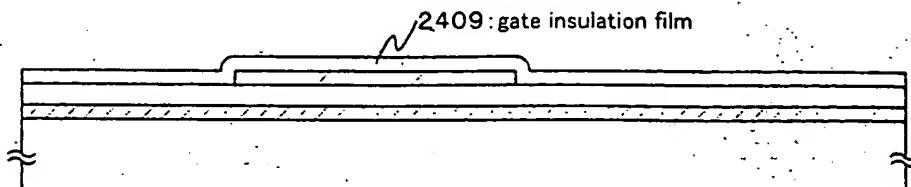


Fig. 18B

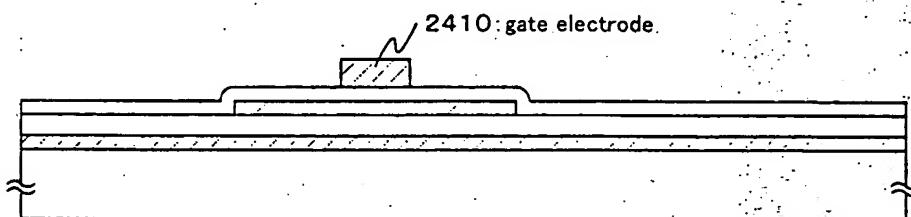


Fig. 18C

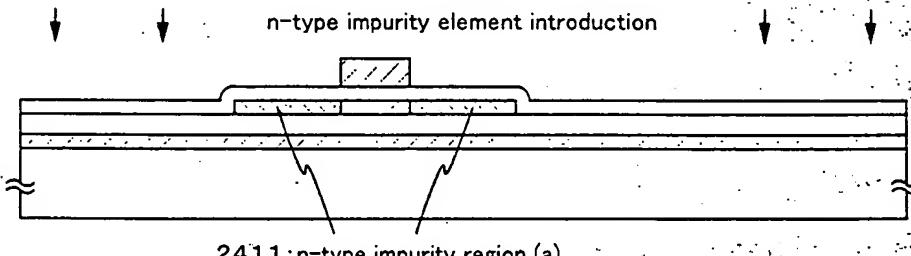


Fig. 18D

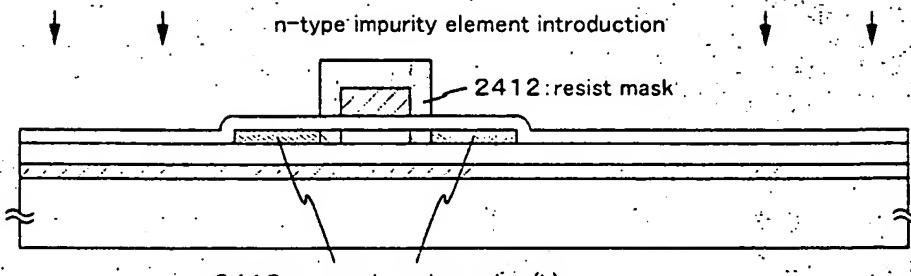


Fig. 19A

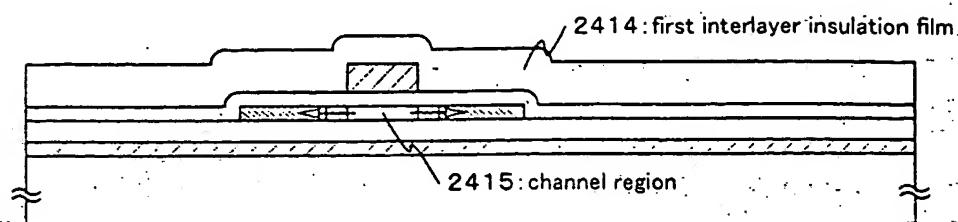


Fig. 19B

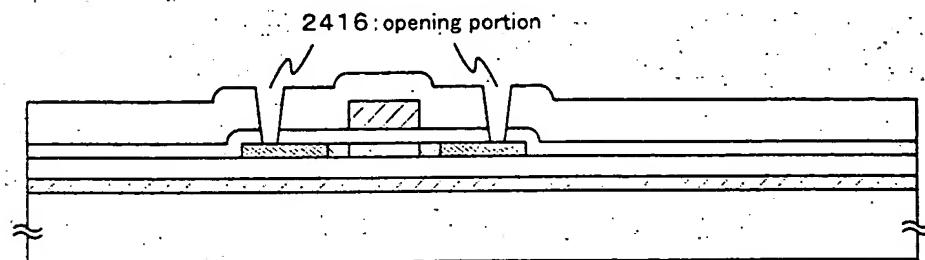


Fig. 19C

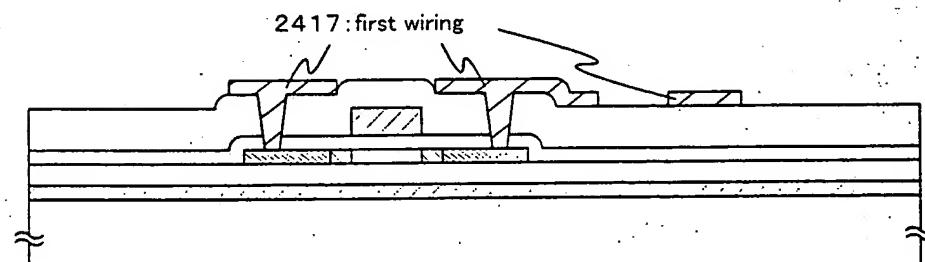


Fig. 19D

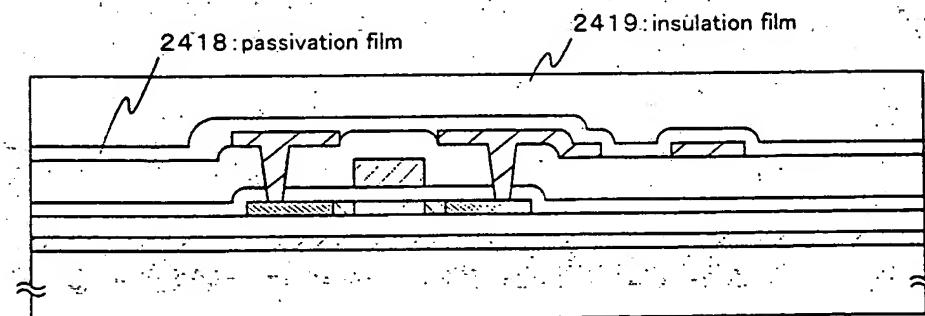


Fig. 20A

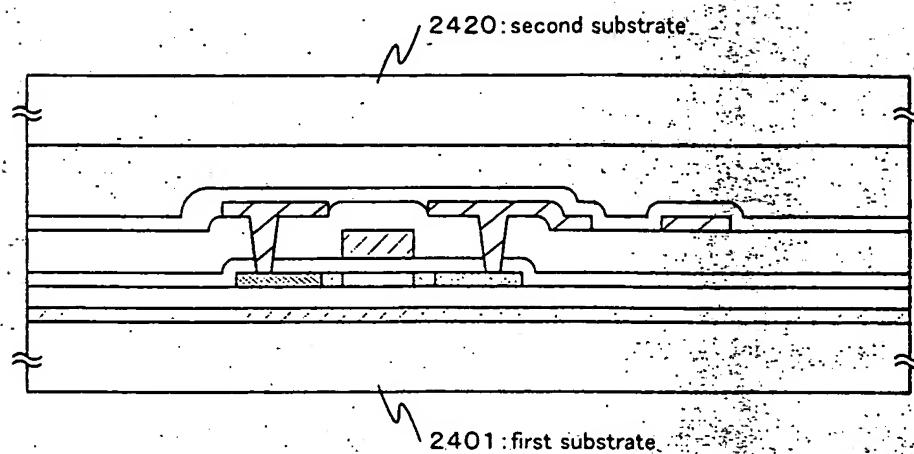


Fig. 20B

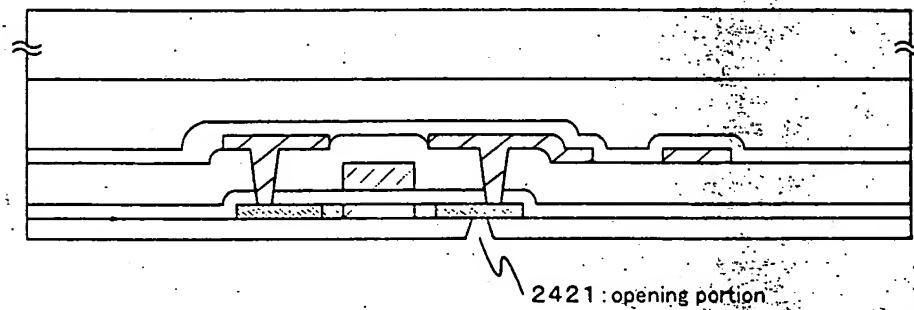
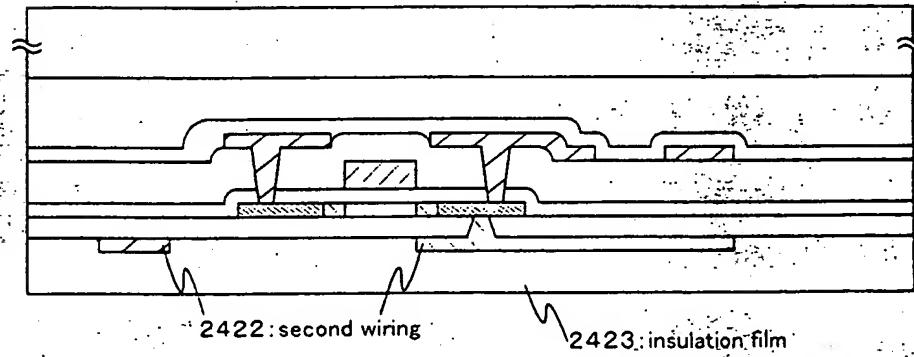


Fig. 20C



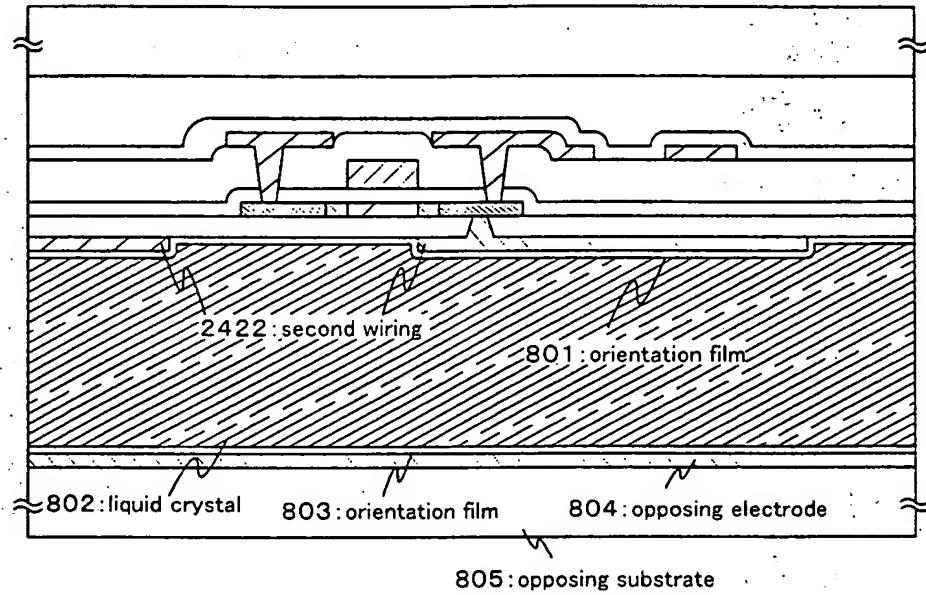


Fig. 21

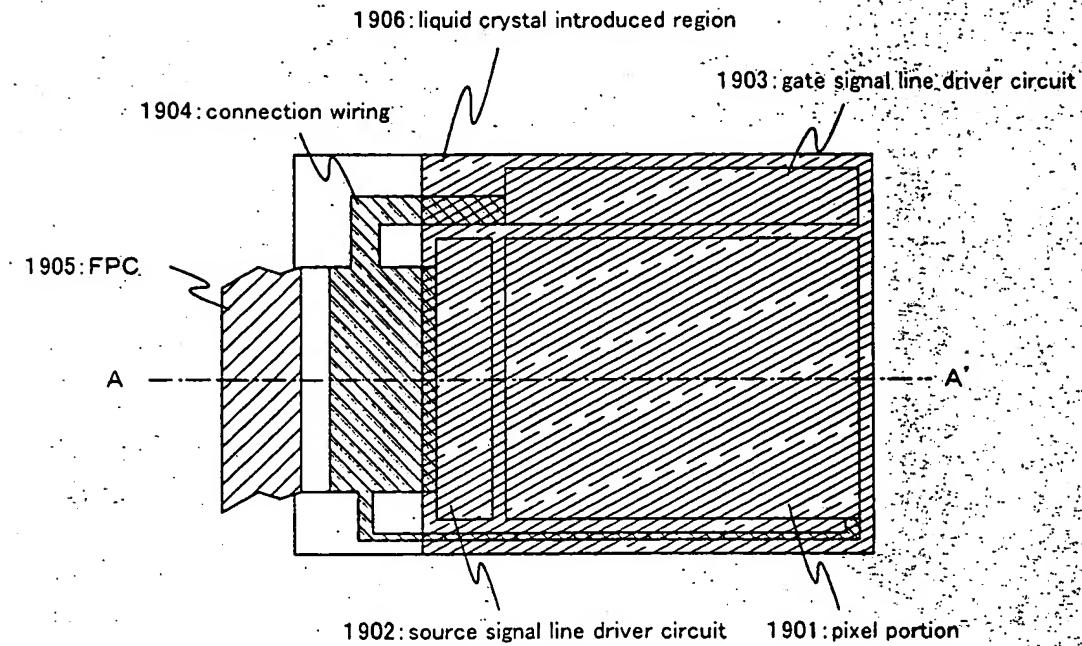


Fig. 22

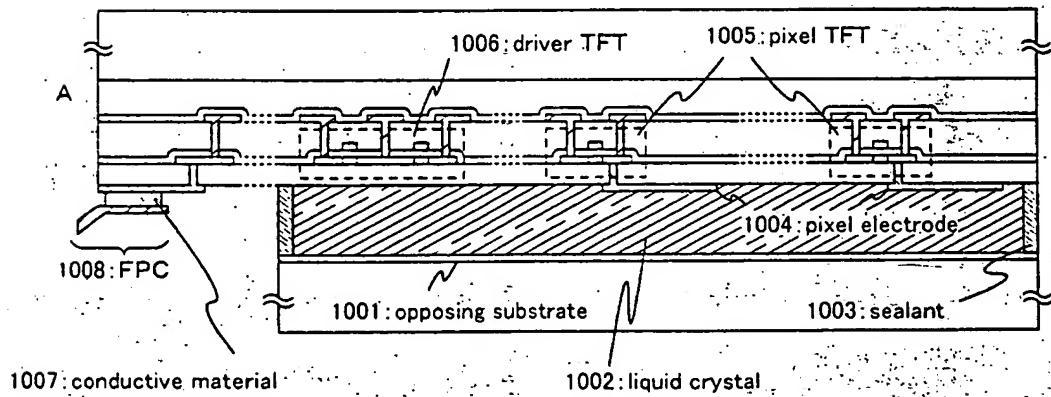


Fig. 23

Fig. 24A

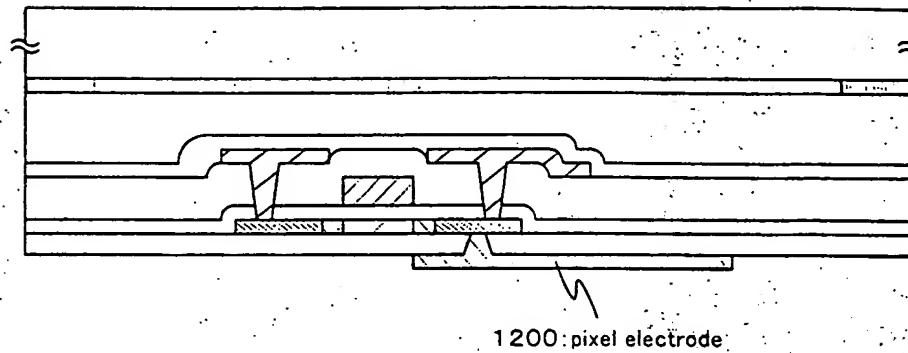


Fig. 24B

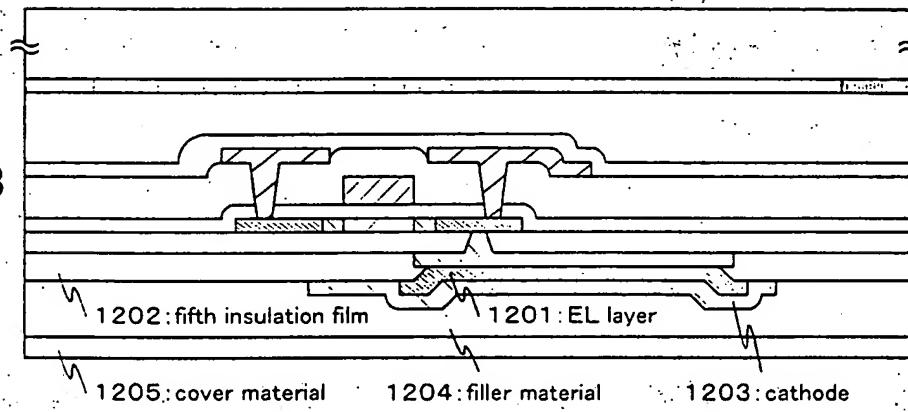
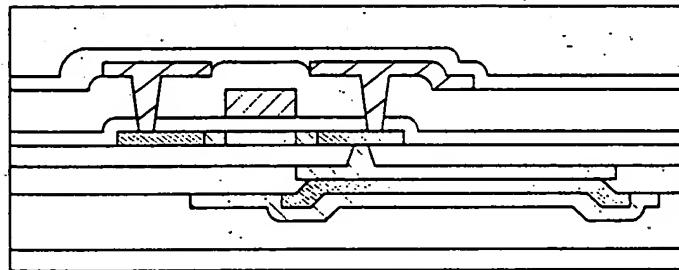


Fig. 24C



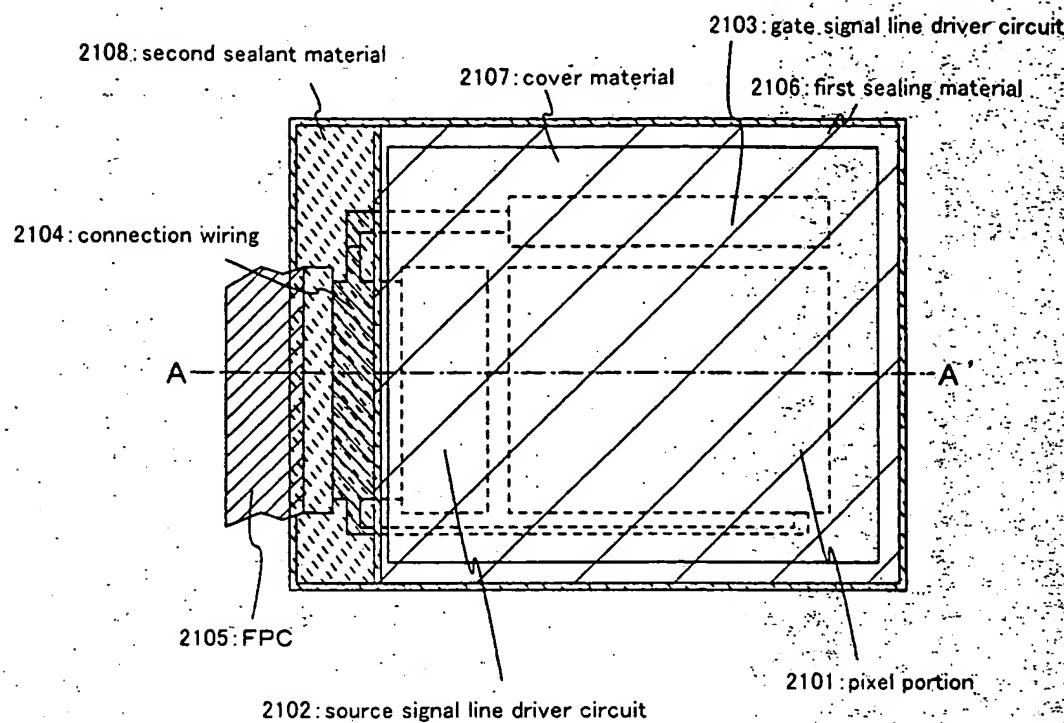


Fig. 25

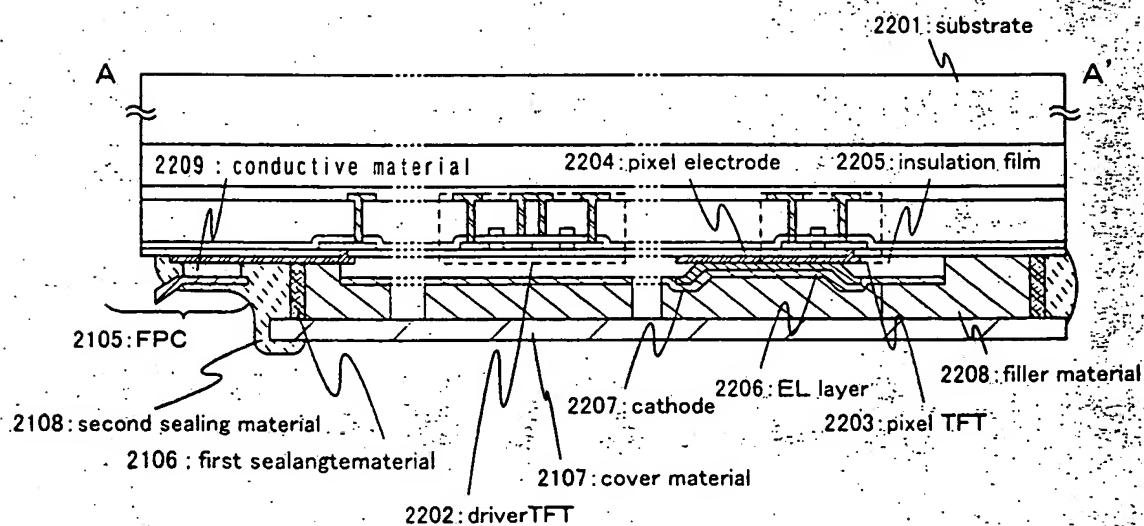


Fig. 26

Applicant(s): Akira Ishikawa

SEMICONDUCTOR DEVICE AND MANUFACTURING

METHOD THEREOF

Attorney Docket No. 12732-075002

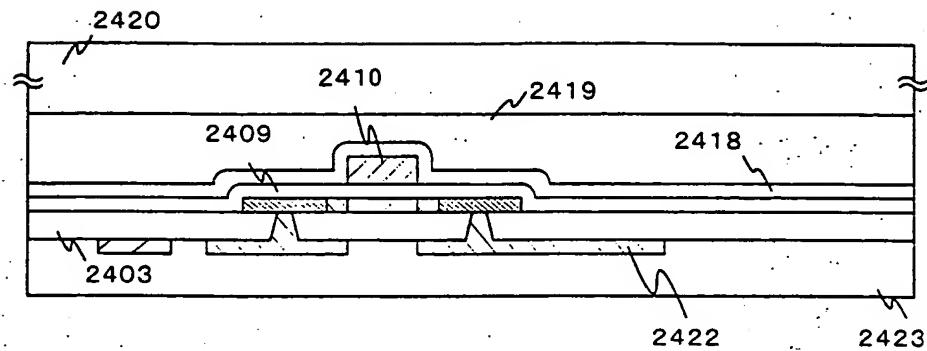


Fig. 27

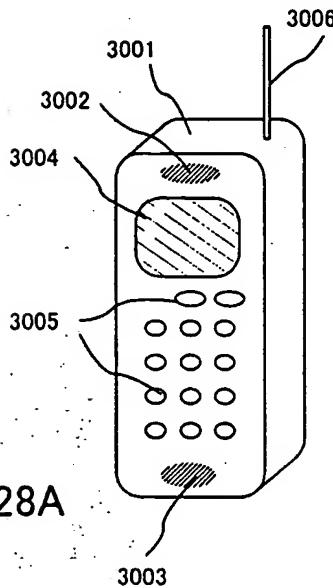


Fig. 28A

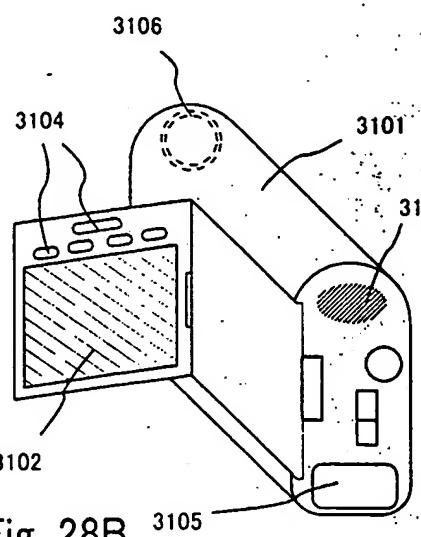


Fig. 28B

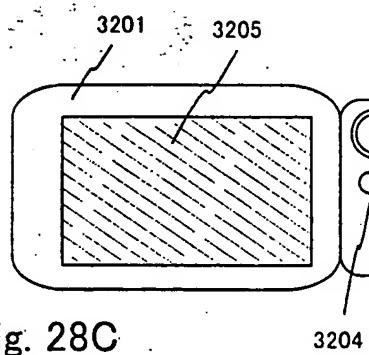


Fig. 28C

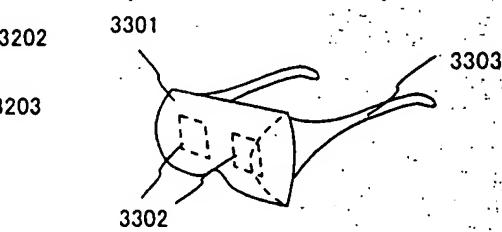


Fig. 28D

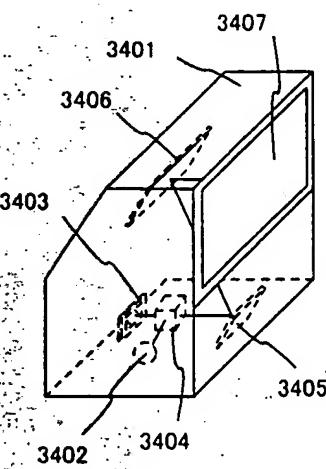


Fig. 28E

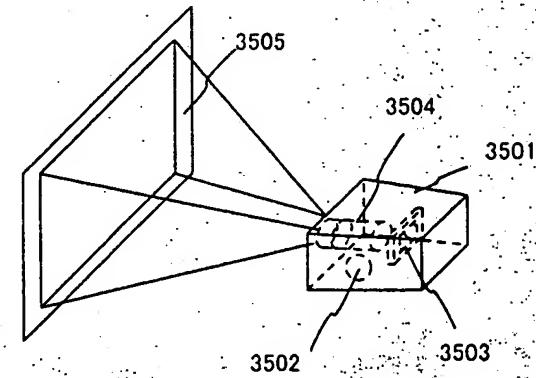


Fig. 28F